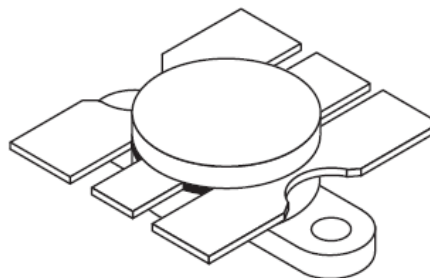


The RF Line NPN Silicon Power Transistor 60 W, 225 - 400 MHz, 28 V

Rev. V1

- Guaranteed performance in 225 to 400 MHz broadband amplifier @ 28 Vdc
Output power = 60 W over 225 to 400 MHz band
Minimum gain = 7.8 dB @ 400 MHz
- Built-in matching network for broadband operation using double match technique
- 100% tested for load mismatch at all phase angles with 30:1 VSWR
- Gold metallization system for high reliability applications

Product Image



CASE 316-01, STYLE 1

Designed primarily for wideband large-signal output amplifier stages in the 225 to 400 MHz frequency range.

MAXIMUM RATINGS*

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	33	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C	P_D	146 0.83	Watts $\text{W}/^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.2	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS* ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 50 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	33	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 50 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 5.0 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	2.0	mAdc

NOTE:

(continued)

1. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as RF amplifiers.

* Indicates JEDEC Registered Data.

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ELECTRICAL CHARACTERISTICS* — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	10	—	100	—
DYNAMIC CHARACTERISTICS					
Output Capacitance ($V_{CB} = 28 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{ob}	—	67	75	pF
BROADBAND FUNCTIONAL TESTS (Figure 6)					
Common-Emitter Amplifier Power Gain ($V_{CC} = 28 \text{ Vdc}$, $P_{out} = 60 \text{ W}$, $f = 225\text{--}400 \text{ MHz}$)	G_{PE}	7.8	8.5	—	dB
Electrical Ruggedness ($P_{out} = 60 \text{ W}$, $V_{CC} = 28 \text{ Vdc}$, $f = 400 \text{ MHz}$, VSWR 30:1 all phase angles)	ψ	No Degradation in Output Power			—
NARROW BAND FUNCTIONAL TESTS (Figure 1)					
Common-Emitter Amplifier Power Gain ($V_{CC} = 28 \text{ Vdc}$, $P_{out} = 60 \text{ W}$, $f = 400 \text{ MHz}$)	G_{PE}	7.8	10	—	dB
Collector Efficiency ($V_{CC} = 28 \text{ Vdc}$, $P_{out} = 60 \text{ W}$, $f = 400 \text{ MHz}$)	η	55	—	—	%

* Indicates JEDEC Registered Data.

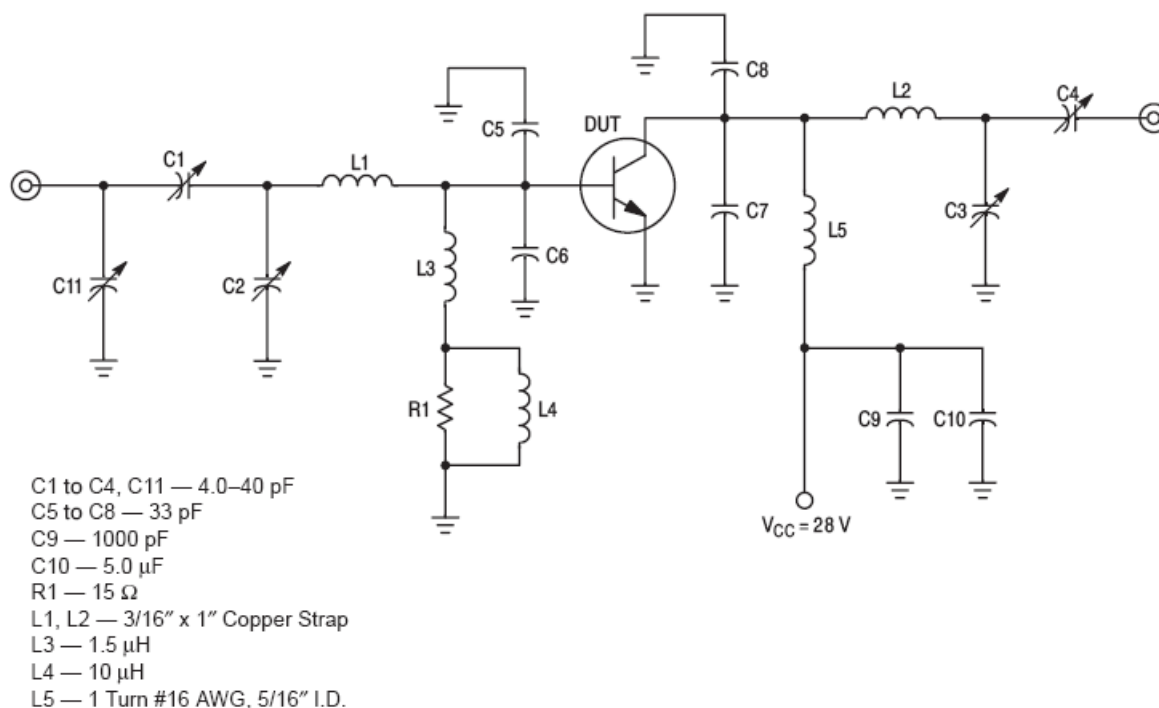


Figure 1. 400 MHz Test Amplifier (Narrow Band)

NARROW BAND DATA

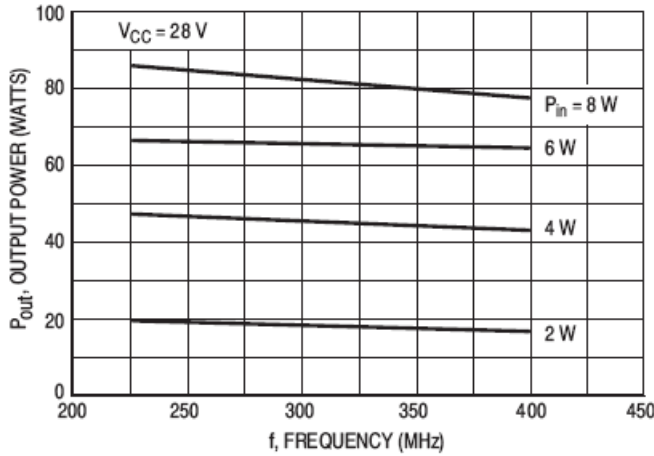


Figure 2. P_{out} versus Frequency

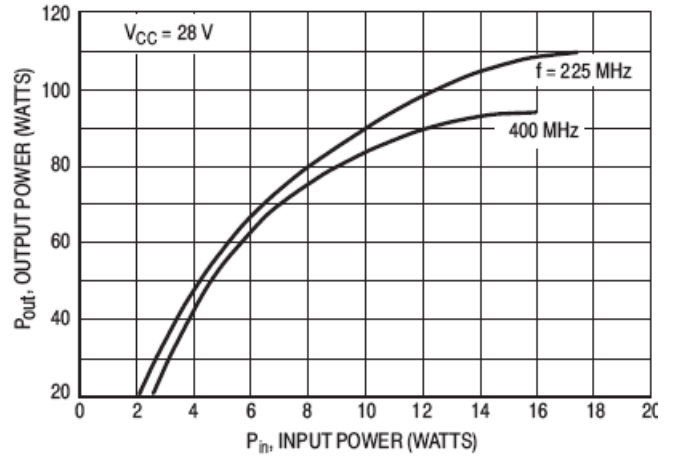


Figure 3. Output Power versus Input Power

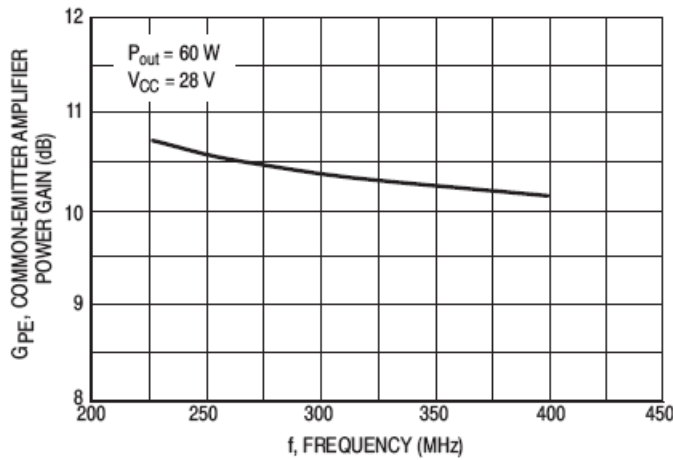


Figure 4. Power Gain versus Frequency

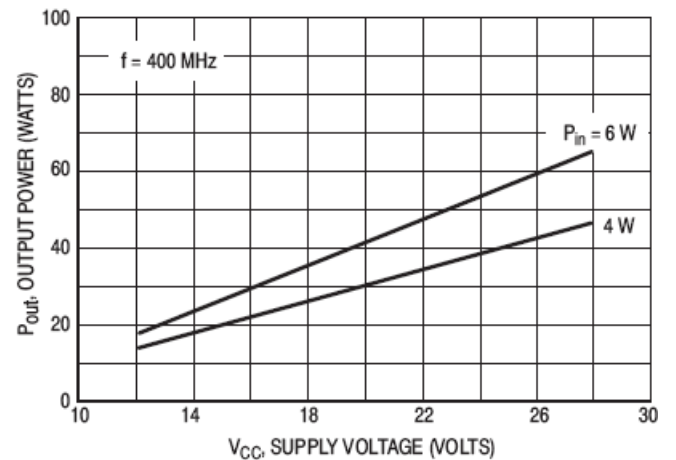


Figure 5. Output Power versus Supply Voltage

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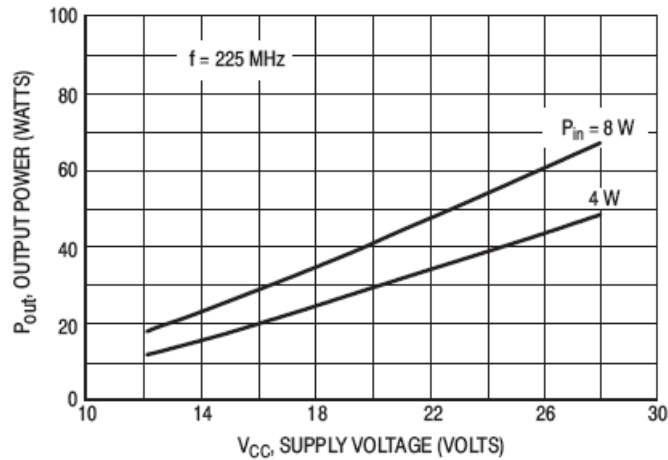
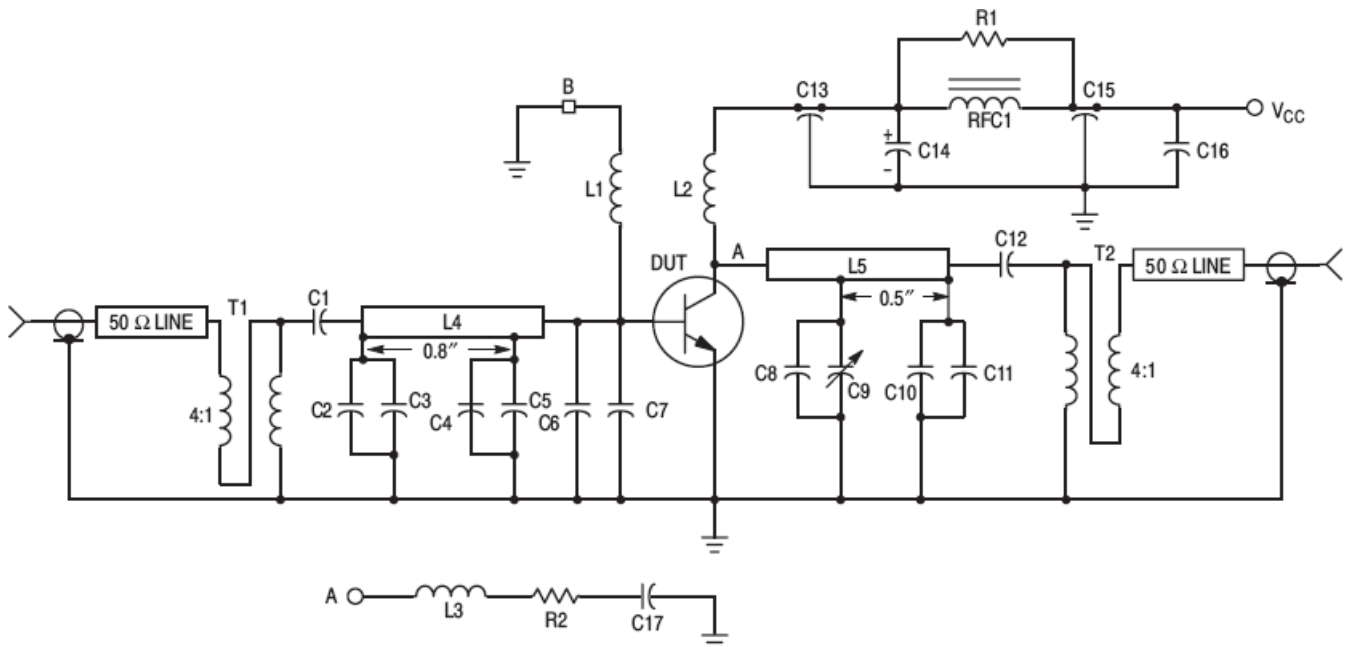


Figure 6. Output Power versus Supply Voltage



C1 — 68 pF
 C2, C4, C8, C10 — 27 pF
 C3, C5, C11 — 10 pF
 C6, C7 — 51 pF
 C9 — 1.0–10 pF JOHANSON
 C12 — 100 pF
 C13, C15 — 680 pF
 C14, C16 — 1.0 μF, 35 V Tantalum
 C17 — 0.1 μF, ERIE Red Cap

RFC1 — Ferrite Bead Choke, Ferroxcube VK200 19/4B
 B — Ferroxcube 56-590-65/4B Ferrite Bead
 T1, T2 — 25 Ohms (UT25) Miniature Coaxial Cable, 1 turn
 R1 — 11 Ω, 1.0 W
 R2 — 20 Ω, 1/4 W
 L1 — 10 Turns, #22 AWG, 1/8" I.D.
 L2 — 4 Turns, #16 AWG, 1/4" I.D.
 L3 — 6 Turns, #24 AWG, 1/8" I.D.
 L4, L5 — 1" x 0.25" Microstrip Line
 Board Material 0.031" Thick Teflon-Fiberglass

Figure 7. 225 to 400 MHz Broadband Test Circuit Schematic

BROADBAND DATA (Circuit, Figure 7)

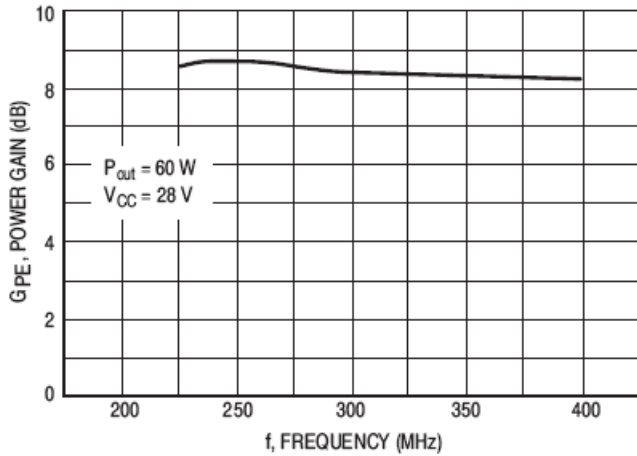


Figure 8. Power Gain versus Frequency

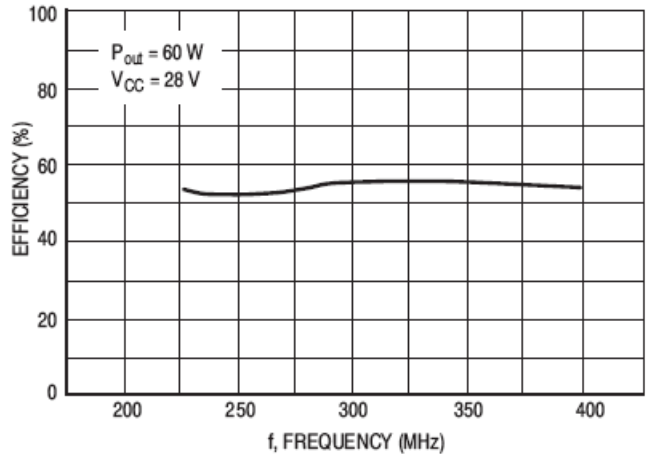


Figure 9. Efficiency versus Frequency

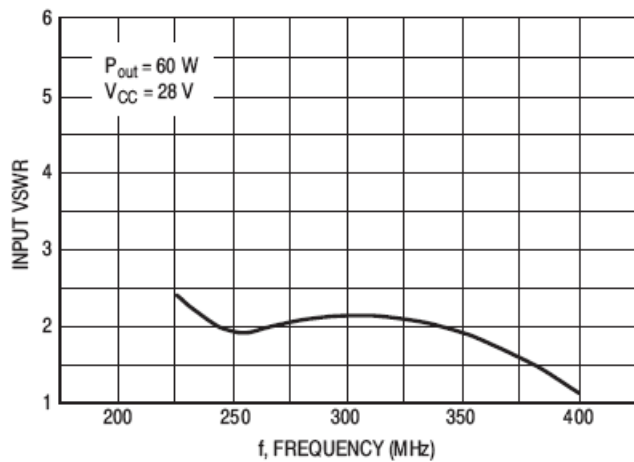


Figure 10. Input VSWR versus Frequency

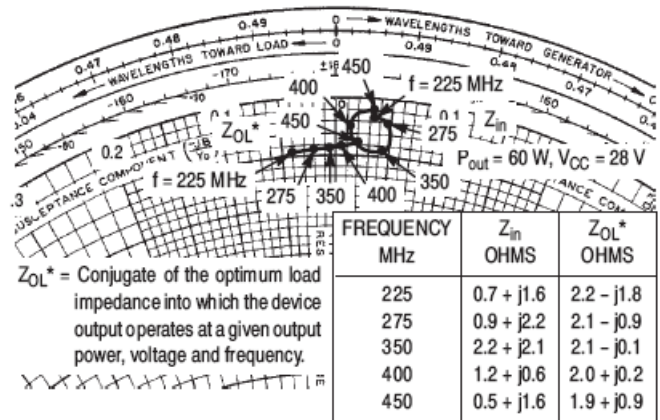


Figure 11. Series Equivalent Input-Output Impedance

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PACKAGE DIMENSIONS

